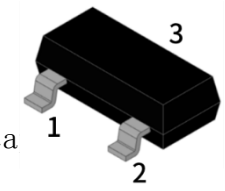
BC3401LST1

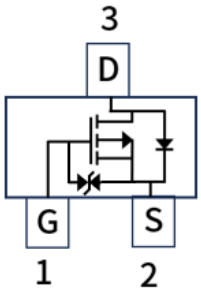
P–Channel MOSFET

1. FEATURES

- The material of product compliance with RoHS requirements and Halogen Free.
- Exceptional on-resistance and maximum DC current. ca
- Load/Power and Interfacing Switching.
- High dense cell design for extremely low RDS(ON).



SOT23 (TO-236)



2. Mechanical Data

- SOT-23 Small Outline Plastic Package.
- Tin plated leads, solderable per J-STD-002 and JESD22-B102.
- Marking: A19T

3. ORDERING INFORMATION

Device	Min Pack	Inner Box	Outer Carton	Reel
BC3401LST1	3000	45000	180000	7 inch

4. MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Value	Unit
Drain–Source Voltage	VDS	-30	V
Drain–Source Voltage	VGS	±12	V
Continuous Drain Current	ID	-4.2	A
Pulsed Drain Current Pulse Limited	IDM	-16.8	A
Power Dissipation	PD	1400	mW

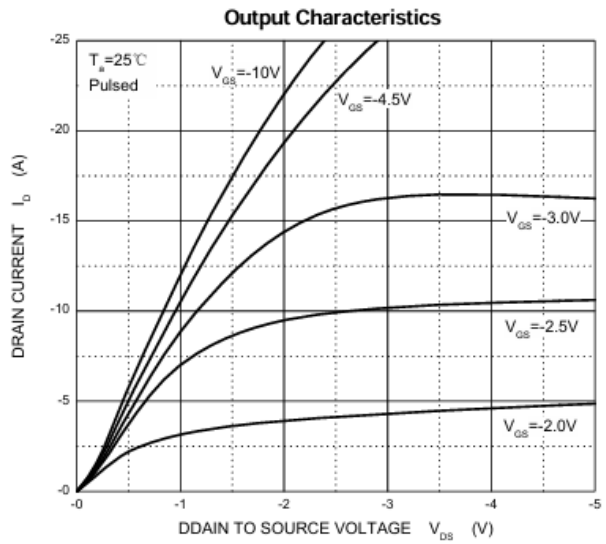
5. THERMAL CHARACTERISTICS

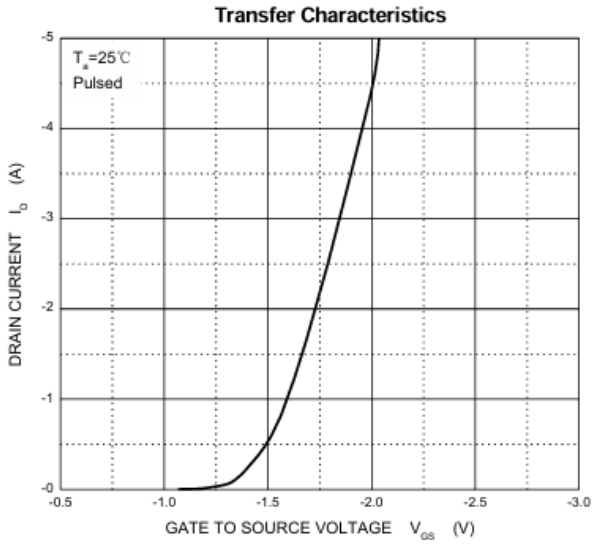
Parameter	Symbol	Limit	Unit
Junction temperature	TJ	150	°C
Storage temperature	TSTG	−55~+150	°C
Thermal Resistance J to A	RθJA	357	°C/W

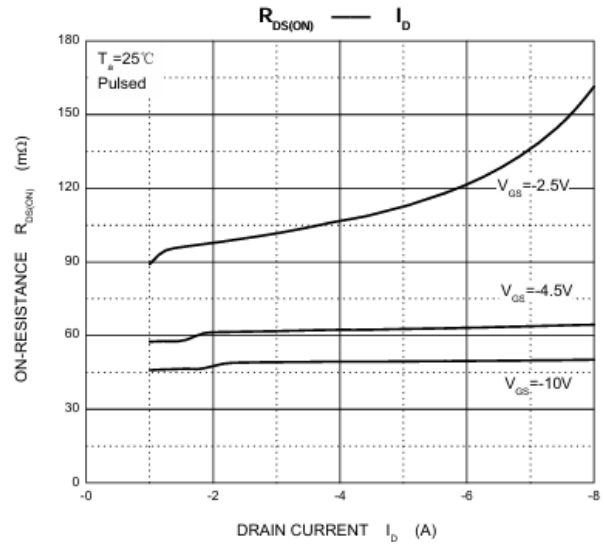
6. MOSFET ELECTRICAL CHARACTERISTICS (Ta= 25°C unless otherwise specified)

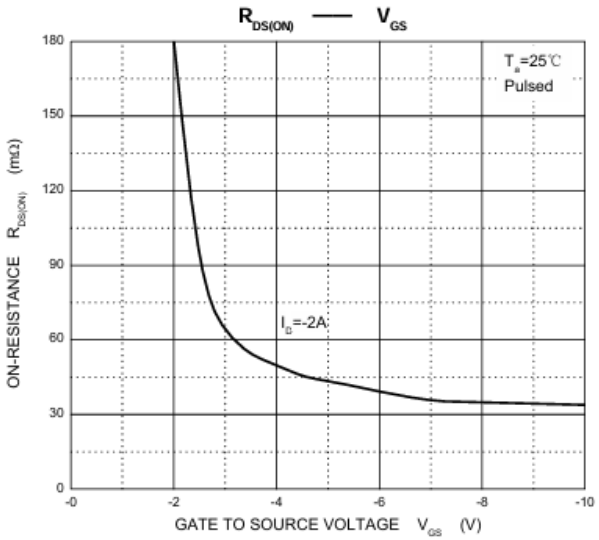
Parameter	Symbol	Condition	Min	TYP	Max	Unit
Drain–Source Breakdown Voltage	VBRDSS	VGS = 0, ID = -250 μA	-30			V
Zero Gate Voltage Drain Current TJ 25°C	IDSS	VGS = 0, VDS = -24 V			-1	μA
Gate–Body Leakage Current,	IGSS	VGS = ±12 V,VDS=0 V			±100	nA
Static Drain–Source On–State Resistance	RDS(on)	VGS = -10 V, ID = -4.2 A		50	65	mΩ
Static Drain–Source On–State Resistance	RDS(on)	VGS =-4.5 V, ID = -4 A		60	75	mΩ
Static Drain–Source On–State Resistance	RDS(on)	VGS=-2.5 V,ID=-1 A		75	90	mΩ
Forward Transconductance	gfs	VDS=-5 V, ID = -5 A	7			S
Gate threshold voltage	VGS（TH）	VDS=VGS,ID=-250uA	-0.6	-0.9	-1.3	V
Input Capacitance	Ciss	VDS = -15 V, VGS = 0, f = 1 MHz		954		PF
Output Capacitance	Coss			115		PF
Reverse Transfer Capacitance	Crss			77		PF
Turn-On Delay Time	Td(on)	VGS = -10 V , VDS=-15 V,RL=3.6 Ω RGEN=6 Ω			6.3	ns
Rise time	Tr				3.2	ns
Turn-Off Delay Time	Td(off)				38.2	ns
Fall time	Tf				12	ns
Diode forwaard voltage	VSD	IS=-1 A,VGS=0			-1	V

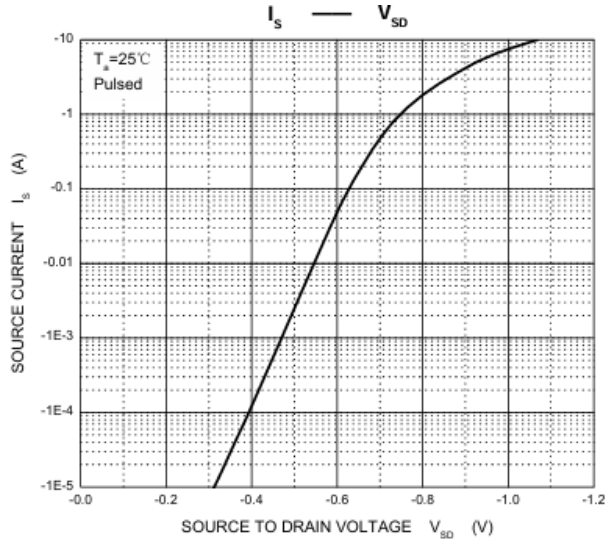
7. ELECTRICAL CHARACTERISTICS CURVES

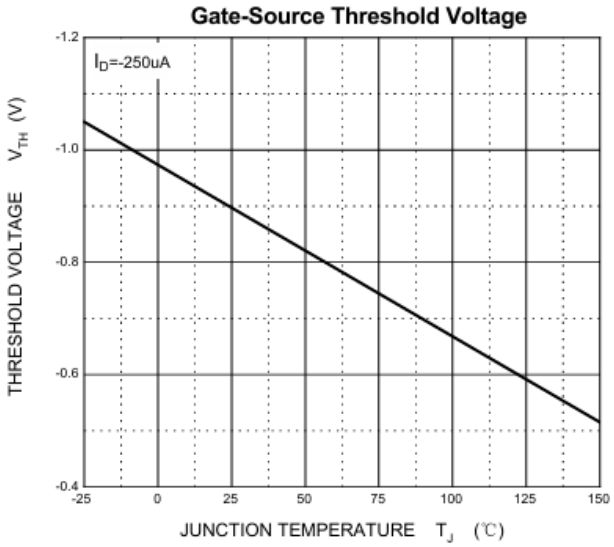




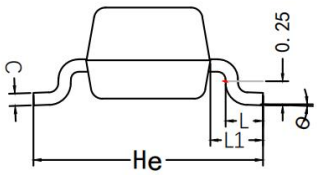


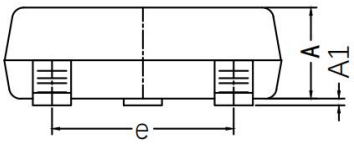


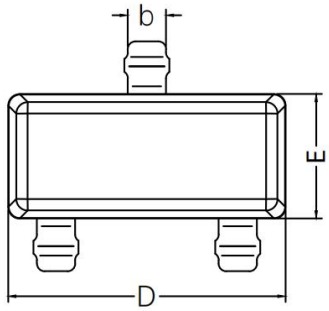




8. OUTLINE AND DIMENSIONS

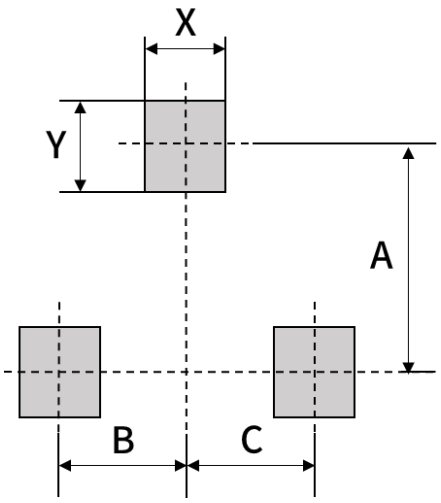






DIM	MIN	NOR	MAX
A	0.85	0.95	1.05
A1	0.01	0.06	0.10
b	0.36	0.44	0.52
c	0.09	0.13	0.18
D	2.80	2.90	3.10
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.40	0.50
L1	0.35	0.50	0.65
He	2.10	2.35	2.50
θ	0°	-	10°
All Dimensions in mm			

9. SUGGESTED PAD LAYOUT



SOT23		
DIM	mm	inch
A	2.00	0.079
B	0.95	0.037
C	0.95	0.037
X	0.80	0.031
Y	0.90	0.035

10. DISCLAIMER

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